NC7WZ125

TinyLogic UHS Dual Buffer with 3-STATE Outputs

ON Semiconductor®

www.onsemi.com

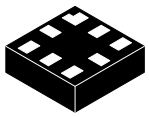
Description

The NC7WZ125 is a Dual Non−Inverting Buffer with independent active LOW enables for the 3−STATE outputs. The Ultra High Speed device is fabricated with advanced CMOS technology to achieve superior switching performance with high output drive while maintaining low static power dissipation over a broad V_{CC} operating range. The device is specified to operate over the 1.65 V to 5.5 V V_{CC} operating range. The inputs and outputs are high impedance when V_{CC} is 0 V. Inputs tolerate voltages up to 5.5 V independent of V_{CC} operating range. Outputs tolerate voltages above V_{CC} when in the 3−STATE condition.

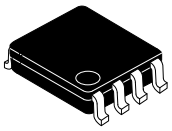
Features

- Space Saving US8 Surface Mount Package
- MicroPak™ Pb−Free Leadless Package
- Ultra High Speed: t_{PD} 2.6 ns Typ. into 50 pF at 5 V V_{CC}
- High Output Drive: ±24 mA at 3 V V_{CC}
- Broad V_{CC} Operating Range: 1.65 V to 5.5 V
- Matches the Performance of LCX when Operated at 3.3 V V_{CC}
- Power Down High Impedance Inputs / Outputs
- Overvoltage Tolerant Inputs Facilitate 5 V to 3 V Translation
- Outputs are Overvoltage Tolerant in 3−STATE Mode
- Proprietary Noise / EMI Reduction Circuitry Implemented
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

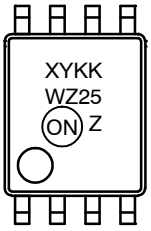
MARKING DIAGRAMS



UQFN8
1.6X1.6, 0.5P
CASE 523AY



US8
CASE 846AN



P3, WZ25	= Specific Device Code
KK	= 2−Digit Lot Run Traceability Code
XY	= 2−Digit Date Code Format
Z	= Assembly Plant Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

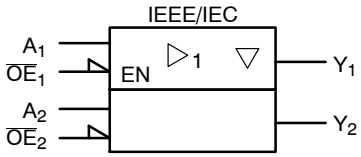


Figure 1. Logic Symbol

Connection Diagrams

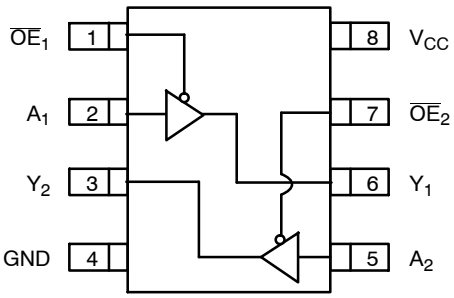


Figure 2. Connection Diagram (Top View)

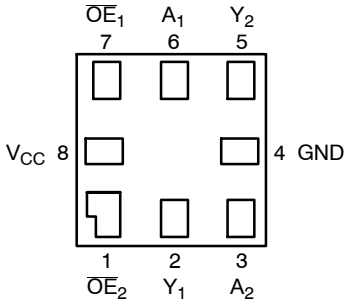


Figure 3. Pad Assignments for MicroPak (Top Thru View)

PIN DESCRIPTIONS

Pin Names	Description
$\overline{OE}_n$	Enable Inputs for 3−STATE Outputs
A_n	Input
Y_n	3−STATE Outputs

FUNCTION TABLE

Inputs		Output
$\overline{OE}$	A_n	Y_n
L	L	L
L	H	H
H	L	Z
H	H	Z

H = HIGH Logic Level
L = LOW Logic Level
Z = 3−STATE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage		−0.5	6.5	V
V_{IN}	DC Input Voltage (Note 1)		−0.5	6.5	V
V_{OUT}	DC Output Voltage		−0.5	6.5	V
I_{IK}	DC Input Diode Current	V_{IN} < 0 V	−	−50	mA
I_{OK}	DC Output Diode Current	V_{OUT} < 0 V	−	−50	mA
I_{OUT}	DC Output Source / Sink Current		−	±50	mA
I_{CC} / I_{GND}	DC V_{CC} / Ground Current		−	±100	mA
T_{STG}	Storage Temperature Range		−65	+150	°C
T_J	Junction Lead Temperature under Bias		−	+150	°C
T_L	Junction Lead Temperature (Soldering, 10 Seconds)		−	+260	°C
P_D	Power Dissipation @ +85°C		−	250	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage Operating		1.65	5.5	V
	Supply Voltage Data Retention		1.5	5.5	
V_{IN}	Input Voltage		0	5.5	V
V_{OUT}	Output Voltage	Active State	0	V_{CC}	V
		3−STATE	0	5.5	V
T_A	Operating Temperature		−40	+85	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} @ 1.8 V ±0.15 V, 2.5 V ±0.2 V	0	20	ns/V
		V_{CC} @ 3.3 V ±0.3 V	0	10	
		V_{CC} @ 5.0 V ±0.5 V	0	5	
θ_{JA}	Thermal Resistance		−	250	°C/W

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

2. Unused inputs must be held HIGH or LOW. They may not float.

DC ELECTICAL CHARACTERISTICS

Symbol	Parameter	Conditions		V_{CC} (V)	T_A = +25°C			T_A = −40 to +85°C		Unit
					Min	Typ	Max	Min	Max	
V_{IH}	HIGH Level Input Voltage			1.65 to 1.95	0.65 V_{CC}	–	–	0.65 V_{CC}	–	V
				2.3 to 5.5	0.7 V_{CC}	–	–	0.7 V_{CC}	–	
V_{IL}	LOW Level Input Voltage			1.65 to 1.95	–	–	0.35 V_{CC}	–	0.35 V_{CC}	V
				2.3 to 5.5	–	–	0.3 V_{CC}	–	0.3 V_{CC}	
V_{OH}	HIGH Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	1.65	1.55	1.65	–	1.55	–	V
				2.3	2.2	2.3	–	2.2	–	
				3.0	2.9	3.0	–	2.9	–	
				4.5	4.4	4.5	–	4.4	–	
		V_{IN} = V_{IH} or V_{IL}	I_{OH} = −4 mA	1.65	1.29	1.52	–	1.29	–	
			I_{OH} = −8 mA	2.3	1.9	2.15	–	1.9	–	
			I_{OH} = −16 mA	3.0	2.4	2.80	–	2.4	–	
			I_{OH} = −24 mA	3.0	2.3	2.68	–	2.3	–	
			I_{OH} = −32 mA	4.5	3.8	4.20	–	3.8	–	
V_{OL}	LOW Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.65	–	0.0	0.10	–	0.10	V
				2.3	–	0.0	0.10	–	0.10	
				3.0	–	0.0	0.10	–	0.10	
				4.5	–	0.0	0.10	–	0.10	
			I_{OL} = 4 mA	1.65	–	0.08	0.24	–	0.24	
			I_{OL} = 8 mA	2.3	–	0.10	0.3	–	0.3	
			I_{OL} = 16 mA	3.0	–	0.15	0.4	–	0.4	
			I_{OL} = 24 mA	3.0	–	0.22	0.55	–	0.55	
			I_{OL} = 32 mA	4.5	–	0.22	0.55	–	0.55	
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V, GND		1.65 to 5.5	–	–	±0.1	–	±1	μA
I_{OZ}	3−STATE Output Leakage	V_{IN} = V_{IH} or V_{IL} 0 ≤ V_{OUT} ≤ 5.5 V		1.65 to 5.5	–	–	±0.5	–	±5	μA
I_{OFF}	Power Off Leakage Current	V_{IN} or V_{OUT} = 5.5 V		0.0	–	–	1	–	10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = 5.5 V, GND		1.65 to 5.5	–	–	1	–	10	μA

NOISE CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = +25°C		Unit
				Typ	Max	
V_{OLP} (Note 3)	Quiet Output Maximum Dynamic V_{OL}	C_L = 50 pF	5.0	–	1.0	V
V_{OLV} (Note 3)	Quiet Output Minimum Dynamic V_{OL}	C_L = 50 pF	5.0	–	1.0	V
V_{OHV} (Note 3)	Quiet Output Minimum Dynamic V_{OH}	C_L = 50 pF	5.0	–	4.0	V
V_{IHD} (Note 3)	Minimum HIGH Level Dynamic Input Voltage	C_L = 50 pF	5.0	–	3.5	V
V_{ILD} (Note 3)	Maximum LOW Level Dynamic Input Voltage	C_L = 50 pF	5.0	–	1.5	V

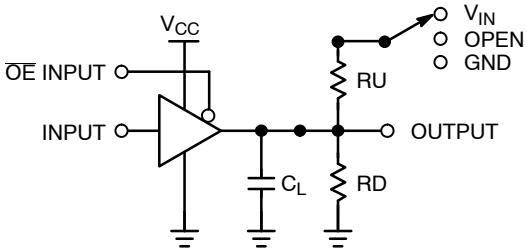
3. Parameter guaranteed by design.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = +25°C			T_A = −40 to +85°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay A_N to Y_N (Figure 4, 6)	C_L = 15 pF, R_D = 1 MΩ, S1 = Open	1.8 ±0.15	–	–	12.0	–	13.0	ns
			2.5 ±0.2	–	–	7.5	–	8.0	
			3.3 ±0.3	–	–	5.2	–	5.5	
			5.0 ±0.5	–	–	4.5	–	4.8	
		C_L = 50 pF, R_D = 500 Ω, S1 = Open	3.3 ±0.3	–	–	5.7	–	6.0	
			5.0 ±0.5	–	–	5.0	–	5.3	
t_{OSLH}, t_{OSHL}	Output to Output Skew (Note 4) (Figure 4, 6)	C_L = 50 pF, R_D = 500 Ω, S1 = Open	3.3 ±0.3	–	–	1.0	–	1.0	ns
			5.0 ±0.5	–	–	0.8	–	0.8	
t_{PZL}, t_{PZH}	Output Enable Time (Figure 4, 6)	C_L = 50 pF, R_D,R_U = 500 Ω, S1 = GND for t_{PZH}, S1 = V_I for t_{PZL}, V_I = 2 x V_{CC}	1.8 ±0.15	–	–	14.0	–	15.0	ns
			2.5 ±0.2	–	–	8.5	–	9.0	
			3.3 ±0.3	–	–	6.2	–	6.5	
			5.5 ±0.5	–	–	5.5	–	5.8	
t_{PLZ}, t_{PHZ}	Output Disable Time (Figure 4, 6)	C_L = 50 pF, R_D,R_U = 500 Ω, S1 = GND for t_{PZH}, S1 = V_I for t_{PZL}, V_I = 2 x V_{CC}	1.8 ±0.15	–	–	12.0	–	13.0	ns
			2.5 ±0.2	–	–	8.0	–	8.5	
			3.3 ±0.3	–	–	5.7	–	6.0	
			5.0 ±0.5	–	–	4.7	–	5.0	
C_{IN}	Input Capacitance		0	–	2.5	–	–	–	pF
C_{OUT}	Output Capacitance		5.0	–	4	–	–	–	pF
C_{PD}	Power Dissipation Capacitance (Figure 5)	(Note 5)	3.3	–	10	–	–	–	pF
			5.0	–	12	–	–	–	

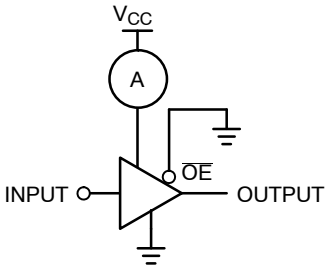
4. Parameter guaranteed by design. $t_{OSLH} = |t_{PLHmax} - t_{PLHmin}|$; $t_{OSHL} = |t_{PHLmax} - t_{PHLmin}|$.
5. C_{PD} is defined as the value of the internal equivalent capacitance which is derived from dynamic operating current consumption (I_{CCD}) at no output loading and operating at 50% duty cycle. (see Figure 5) C_{PD} is related to I_{CCD} dynamic operating current by the expression: $I_{CCD} = (C_{PD})\ (V_{CC})\ (f_{IN}) + (I_{CC}static)$.

AC Loading and Waveforms



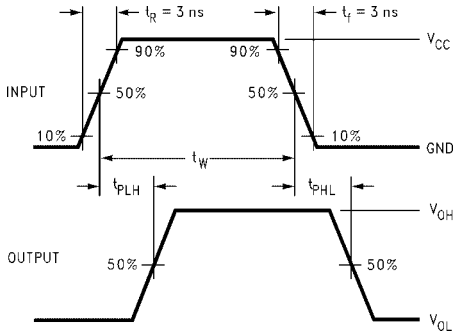
C_L includes load and stray capacitance
Input PRR = 1.0 MHz; t_W = 500 ns

Figure 4. AC Test Circuit



Input = AC Waveform; $t_r = t_f$ = 1.8 ns;
PRR = 10 MHz; Duty Cycle = 50%.

Figure 5. I_{CCD} Test Circuit



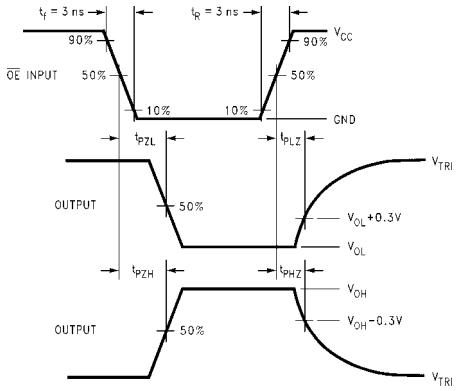


Figure 6. AC Waveforms

ORDERING INFORMATION

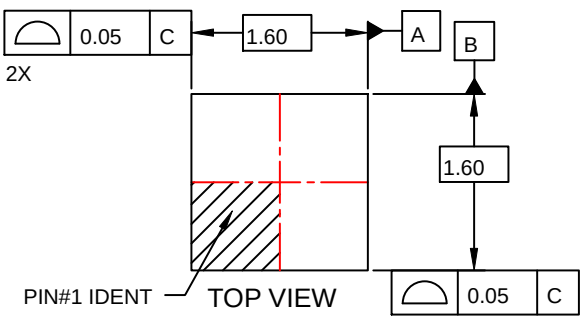
Order Number	Top Mark	Package	Shipping†
NC7WZ125K8X	WZ25	8−Lead US8, JEDEC MO−187, Variation CA 3.1 mm Wide	3000 / Tape & Reel
NC7WZ125L8X	P3	8−Lead MicroPak, 1.6 mm Wide (Pb−Free)	5000 / Tape & Reel

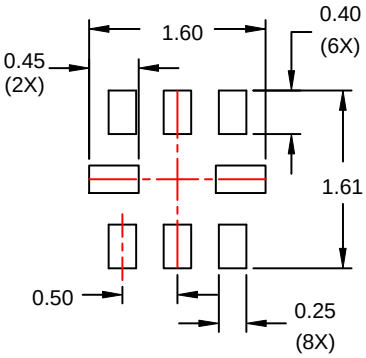
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

6. Pb−Free package per JEDEC J−STD−020B.

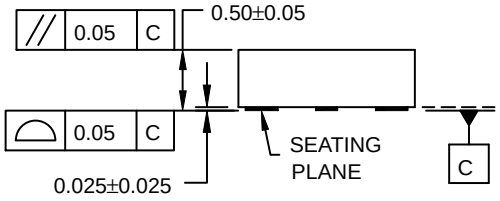
UQFN8 1.6X1.6, 0.5P
CASE 523AY
ISSUE O

DATE 31 AUG 2016





RECOMMENDED
LAND PATTERN



SIDE VIEW

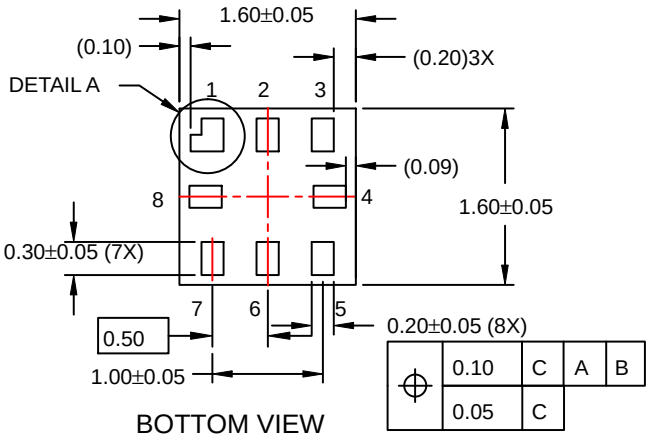
NOTES:

A. PACKAGE CONFORMS TO JEDEC MO−255 VARIATION UAAD.

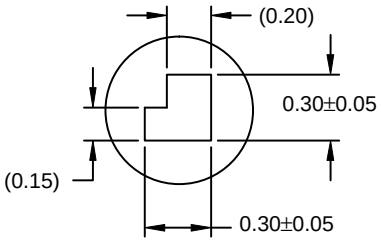
B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.



BOTTOM VIEW



DETAIL A
SCALE : 2X

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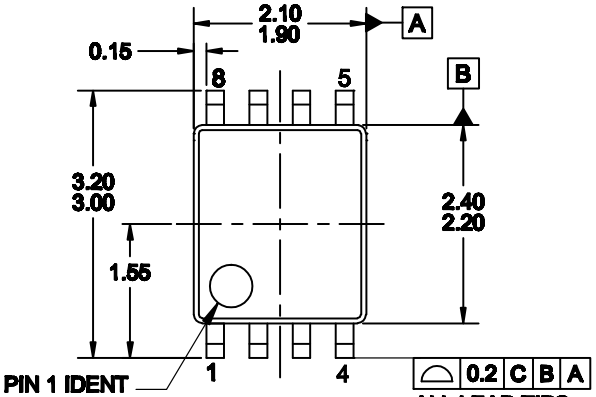
DESCRIPTION:	**UQFN8 1.6X1.6, 0.5P**		**PAGE 1 OF 2**

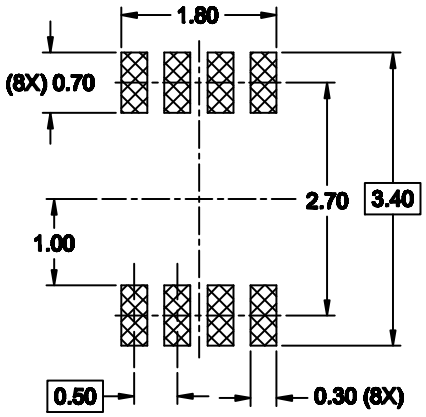
ISSUE	REVISION	DATE
O	RELEASED FOR PRODUCTION FROM FAIRCHILD MAC08A TO ON SEMICONDUCTOR. REQ. BY B. MARQUIS.	31 AUG 2016

US8
CASE 846AN
ISSUE O

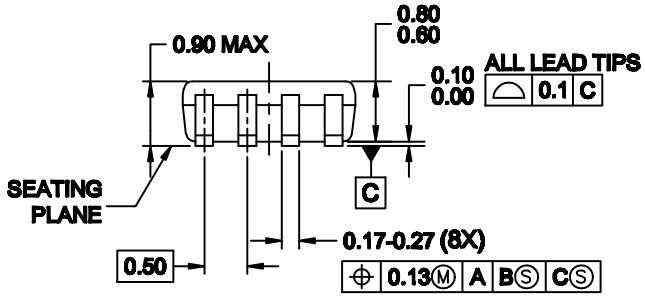
DATE 31 DEC 2016



TOP VIEW



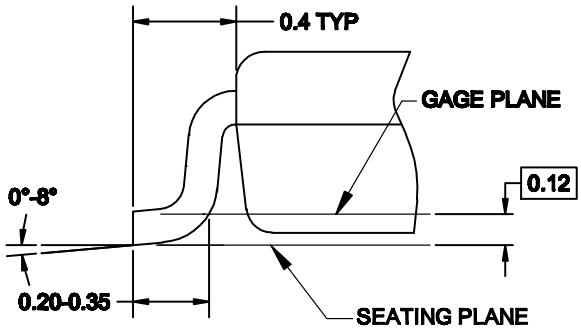
RECOMMENDED LAND PATTERN



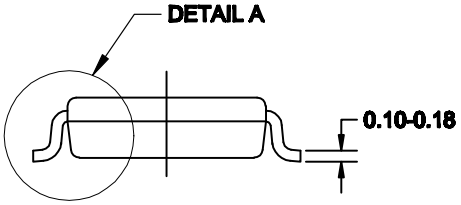
SIDE VIEW

NOTES:

A. CONFORMS TO JEDEC REGISTRATION MO-187
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
D. DIMENSIONS AND TOLERANCES PER ANSI Y14.5M, 1994.



DETAIL A



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NEW STANDARD:			
DESCRIPTION:	**US8**		**PAGE 1 OF 2**

ISSUE	REVISION	DATE
O	RELEASED FOR PRODUCTION FROM FAIRCHILD MKT−MAB08A TO ON SEMI-CONDUCTOR. REQ. BY I. HYLAND.	31 DEC 2016

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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